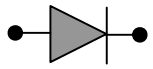
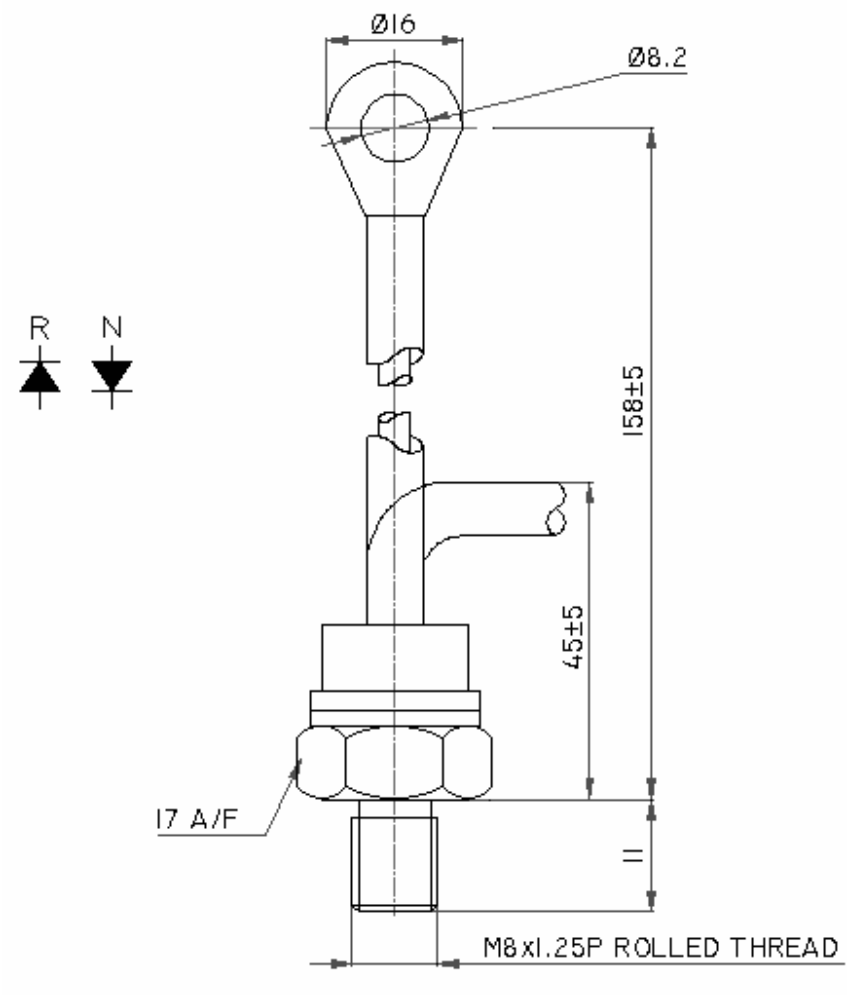
Rectifier Diode SXXHN/HR55

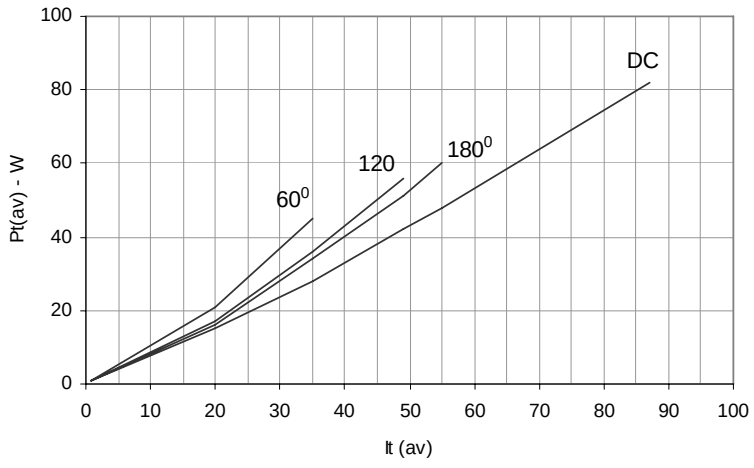


Symbol	Characteristics	Conditions	T_J(^{0}C)	Value	Unit
BLOCKING PARAMETERS					
V_{RRM}	Repetitive peak reverse voltage		180	200-1500	V
I_{RRM}	Repetitive peak reverse current	V = V_{RRM}	180	8	mA
CONDUCTING PARAMETERS					
$I_{F(AV)}$	Average on-state current	180 sine, 50H$_Z$, T_C = 125^{0}C		55	A
I_{RMS}	RMS on-state current			86	A
I_{FSM}	Non repetitive peak surge on-state current	Sine wave, 10mS without reverse voltage	180	800	A
I^2t	Permissible surge energy			3200	A^2S
V_{FM}	Peak on-state voltage drop	On-state current = 172A	180	1.35	V
V_0	Typical forward conduction Threshold voltage		180	0.72	V
r_0	Typical forward slope resistance		180	2.75	mΩ
THERMAL & MECHANICAL PARAMETERS					
$R_{TH\ (J-C)}$	Thermal impedance, 180^0 conduction, Sine	Junction to case		0.50	^{0}C/W
$R_{TH\ (C-HK)}$	Thermal impedance	Case to heatsink		0.15	^{0}C/W
T_J	Maximum Permissible junction temperature			180	^{0}C
T_{STG}	Storage temperature range			-40 – 180	^{0}C
F	Mounting Torque			4.5	NM
W	Weight			40	gms

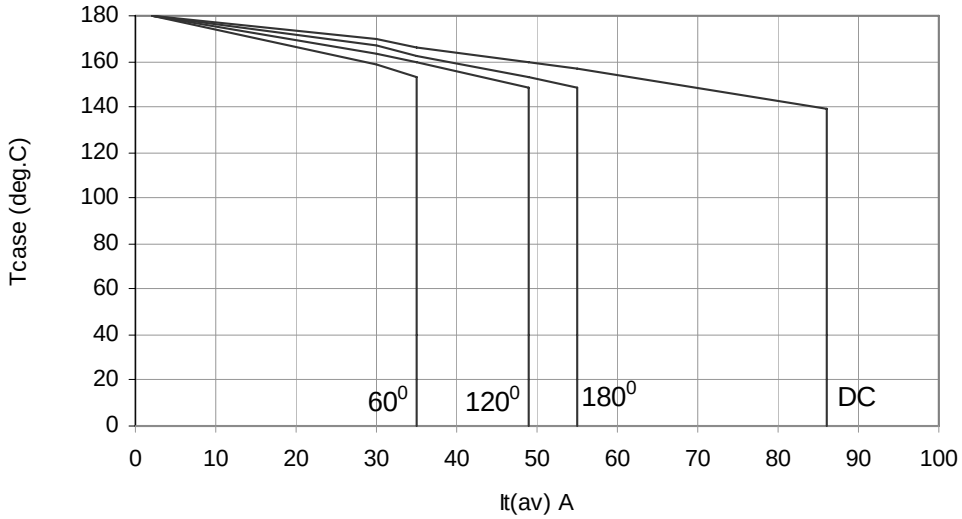


All dimensions in mm

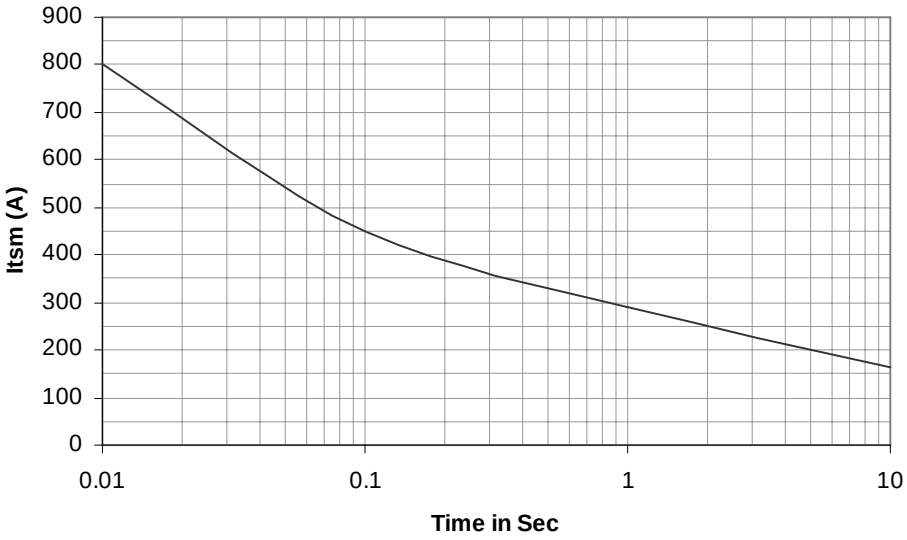
On State Power Loss



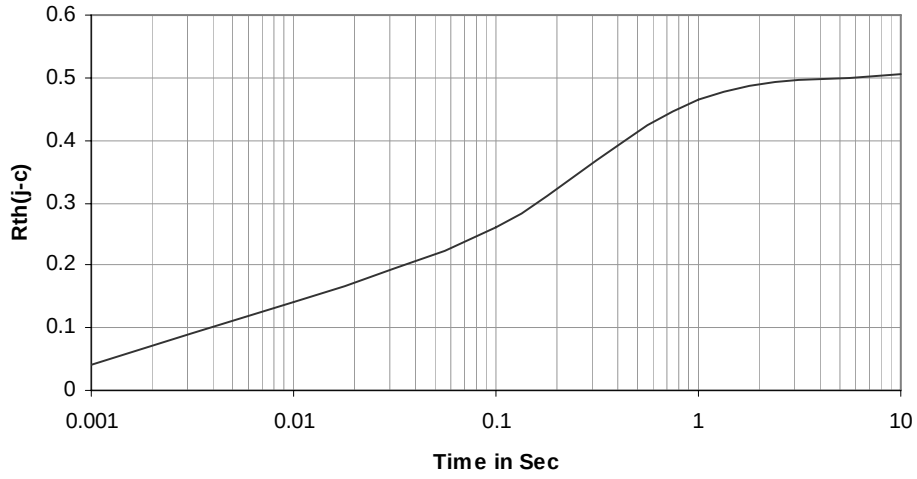
Maximum Permissible Case Temp



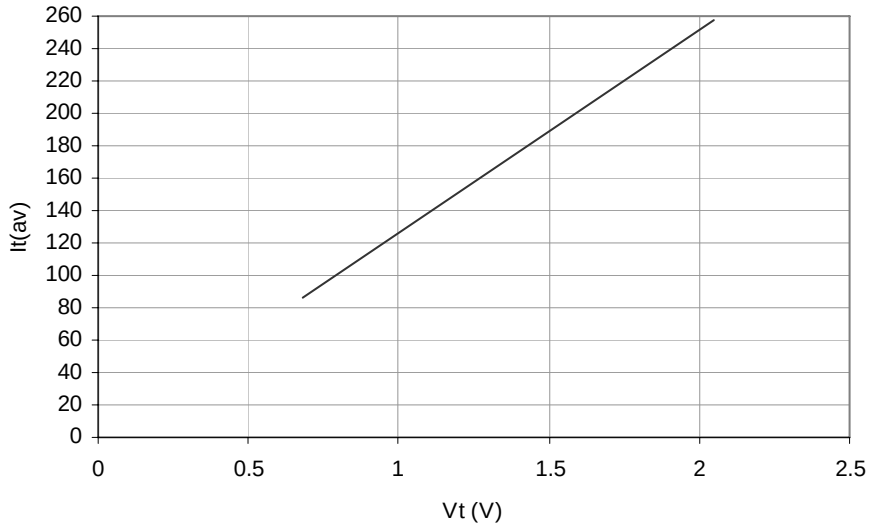
Max non repetitive Surge Current

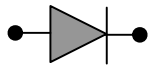


Transient Thermal Impedance Junction to Case



On State Characteristics





Ordering Information: -

S	XX	HN / HR	55
Hirect make Rectifier Diode	V_{RRM} = XX * 100 e.g.12 * 100 =1200V	HN – Normal Polarity HR – Reverse Polarity	$I_{F(AV)}$ = 55A

Hind Rectifiers Ltd reserves the right to change the specifications without notice.

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